

D. Thin Film Process Technology 분과

2020년 2월 13일(목), 10:45-12:30 / Room K (다이아몬드 I, 6층)

■ [TK2-D] Thin Film Process II

좌장: 김우희 교수 (한양대학교), 한정환 교수 (서울과학기술대학교)

TK2-D-1 10:45-11:15	<p>[초청]</p> <p>Strategies for Stabilization of Metastable Phases in Atomic Layer Deposition</p> <p>Seong Keun Kim <i>Center for Electronic Materials, KIST</i></p>
TK2-D-2 11:15-11:30	<p>Hollow Cathode Plasma Source를 이용한 고품질 SiN ALD 공정</p> <p>Jae Chan Park¹, Dae Hyun Kim², Tae Jun Seok¹, Dae Woong Kim¹, Woo-Hee Kim¹, and Tae Joo Park^{1,2}</p> <p>¹<i>Department of Materials Science and Chemical Engineering, Hanyang University,</i> ²<i>Department of Advanced Materials Engineering, Hanyang University</i></p>
TK2-D-3 11:30-11:45	<p>Low-temperature Atomic Layer Deposition of Silicon Nitride Film Using Silicon Halide Precursors</p> <p>신종우¹, 문찬희¹, 하제영¹, 유능경², 송봉근², 이한보람¹</p> <p>¹<i>인천대학교 신소재공학과, ²홍익대학교 화학공학과</i></p>
TK2-D-4 11:45-12:00	<p>N₂H₄를 이용한 저온 Thermal ALD SiN 박막 공정</p> <p>Jae Chan Park¹, Dae Hyun Kim², Tae Jun Seok¹, Dae Woong Kim¹, Woo-Hee Kim¹, and Tae Joo Park^{1,2}</p> <p>¹<i>Department of Materials Science and Chemical Engineering, Hanyang University,</i> ²<i>Department of Materials Science and Chemical Engineering, Hanyang University</i></p>
TK2-D-5 12:00-12:15	<p>Growth Behavior and Properties of Ru Film by Electric Field/Potential Assisted Atomic Layer Deposition (EA-ALD)</p> <p>Ji won Han and Tae Joo Park <i>Department of Materials Science and Chemical Engineering, Hanyang University</i></p>
TK2-D-6 12:15-12:30	<p>Improvement in the Surface Morphology of the Bottom Ru Electrode for DRAM Capacitor</p> <p>Dae Seon Kwon, Dong Gun Kim, Junil Lim, Tae Kyun Kim, Haeng Ha Seo, and Cheol Seong Hwang <i>Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University</i></p>